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Dated: July 7, 2006

Signature: 

(Darren M. Simon)

Docket No.: OCIRS 3.0-088
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Jian H. Zhao

Application No.: 10/671,233

Group Art Unit: 2826

Filed: September 25, 2003

Examiner: T. N. Tran

For: VERTICAL JUNCTION FIELD EFFECT
POWER TRANSISTOR

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

It is respectfully requested that the references listed on the enclosed form be made of record and considered with respect to the above-referenced U.S. patent application. Submission of the present Information Disclosure Statement should not be taken as an admission that the cited references are legally available prior art or that the same are pertinent or material.

In the event that any fee is due in connection with the present Information Disclosure Statement, the Commissioner is hereby authorized to charge the same to our Deposit Account No. 12-1095.

Dated: July 7, 2006

Respectfully submitted,

By: 

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P.O. Box 1450
Alexandria, VA 22313-1450

REQUEST FOR CONSIDERATION OF INFORMATION UNDER 37 CFR § 1.97 (C)

Dear Sir:

It is respectfully requested that the references cited in the enclosed form be considered pursuant to 37 C.F.R. § 1.97(c). Please charge deposit account No. 12-1095 in the amount of \$180.00 pursuant to 37 C.F.R. § 1.17(p). In the event that any additional fee is due in connection with the present request, the same should be charged to our deposit account No. 12-1095.

Dated: July 7, 2006

Respectfully submitted,

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PTO/SB/08a/b (07-05)

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Sheet	1	of	1	Attorney Docket Number	OCIRS 3.0-088
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Complete if Known

Application Number	10/671,233-Conf. #8199
Filing Date	September 25, 2003
First Named Inventor	Jian H. Zhao
Art Unit	2826
Examiner Name	T. N. Tran
Attorney Docket Number	OCIRS 3.0-088

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
	AA	US-6,107,649	08-22-2000	Jian H. Zhao	Column 1, Figure 6A
	AB	US-5,903,020	05-11-99	Richard R. Siegiej, et al.	Fig. 3, Fig. 5, Fig. 10

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				

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NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	CC	K. ASANO, et. al, 5kV 4H-SiC SEJFET with Low RonS of 69 m-ohm-cm2, Proc. of 14 th Intl. Symp. on Power Semiconductor Devices & IC 2002, June 3, 2002, pp. 61-64, IEEE, Piscataway, NJ, USA.	
	CD	J. Nishizawa, et. al., The 2.45 GHz 35 W CW SI recessed gate type SIT with high gain and high voltage operation, IEEE Trans. on Electron Devices, Feb. 2000, pp. 482-487, Vol. 4, No. 2, IEEE, Piscataway, NJ, USA	
	CE	H. Onose, et. al., 2KV 4H-SiC junction FETs, Materials Science Forum, 2002, pp. 1227-1230, Vols. 389-393, Trans Tech Publications, Switzerland	
	CF	Jian H. Zhao et. al, 3.6 m-ohm-cm2, 1,726 4H-SiC normally-off trench-and-implanted vertical JFETs, 2003, pp. 50-52, ISPSD, IEEE, Piscataway, NJ, USA	
	CG	Jian H. Zhao, et al., Demonstration of a high performance 4H-SiC vertical junction field effect transistor without epitaxial regrowth, Feb. 2003, pp. 321-323, Electronics Letters, IEE, Stevenage, SG1 2SD, UK.	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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